

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,112,504 B2
APPLICATION NO. : 10/694684
DATED : September 26, 2006
INVENTOR(S) : Ping-Yi Hsin and Zin Chein Wei

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

On Title Page

Item (75) Inventors: delete "Zan Chun Wei" and insert therefore -- Zin Chein Wei --.

Item (57) ABSTRACT delete entire abstract and insert:

-- A method of forming a MIM capacitor, and the resultant MIM capacitor, comprising the following steps. A structure having a metal structure formed thereover is provided. A dielectric layer is formed over the metal structure and a top layer is formed over the dielectric layer. A capacitance trench is formed through the top layer and into the dielectric layer. Respective bottom electrodes are formed over the opposing side walls of the capacitance trench. A capacitance dielectric layer is formed over: the respective bottom electrodes: the bottom of the capacitance trench; and the remaining top layer. Respective opposing initial via openings are formed adjacent the capacitance trench. Respective trench openings are formed above, continuous and contiguous with the lower portions of the respective opposing initial via openings and exposing portions of the underlying metal structure to form respective opposing dual damascene openings. Planarized metal portions are formed within: the dual damascene openings; and the capacitance trench to form a top electrode. --

Column 4, Line 19, after "16" insert -- are etched --.

Column 4, line 25, after "12" insert -- and bottom electrodes 30', 30". Capacitance trench 25 includes sidewalls 50 formed of remaining portions of capacitance dielectric layer 32". --

Column 4, line 57, delete "Prestent" and insert therefore -- Present --.

Signed and Sealed this

Seventh Day of August, 2007



JON W. DUDAS
Director of the United States Patent and Trademark Office